TOSHIBA SCHOTTKY BARRIER DIODE SCHOTTKY BARRIER TYPE

3 F W J 4 2 N

HIGH SPEED RECTIFIER APPLICATIONS

Unit in mm

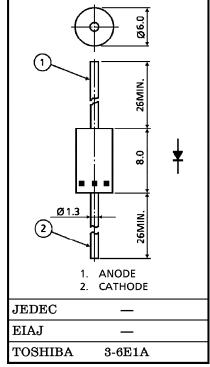
Average Forward Current $: I_{F(AV)} = 3.0A$

Low Forward Voltage $: V_{FM} = 0.37V \text{ (Max.)}$

Repetitive Peak Reverse Voltage: $V_{RRM} = 30V$

MAXIMUM RATINGS

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|--|---------------------|-----------|----------------------|
| Repetitive Peak Reverse Voltage | v_{RRM} | 30 | V |
| Average Forward Current | I _{F (AV)} | 3.0 | Α |
| Peak One Cycle Surge Forward Current (Non-Repetitive) | $I_{	ext{FSM}}$ | 90 (50Hz) | A |
| Junction Temperature | T_{j} | -40~125 | °C |
| Storage Temperature Range | ${ m T_{stg}}$ | -40~125 | $^{\circ}\mathrm{C}$ |

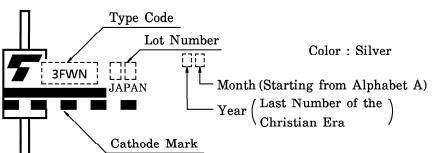


Weight: 1.18g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|------------------------------------|-------------------|-------------------------------------|------|------|------|------|
| Peak Forward Voltage | $V_{\mathbf{FM}}$ | $I_{\mathbf{FM}}\!=\!3.0\mathrm{A}$ | _ | _ | 0.37 | V |
| Repetitive Peak Reverse Current | I_{RRM} | $V_{ m RRM}$ =30 V | _ | _ | 5.0 | mA |
| Junction Capacitance | Cj | $V_R=10V$, $f=1MHz$ | _ | 140 | _ | pF |

MARKING



| CODE | TYPE |
|------|---------|
| 3FWN | 3FWJ42N |

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